



#### **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
-20V	1.9Ω @ V <sub>GS</sub> = -4.5V	-0.36A
	2.4Ω @ V <sub>GS</sub> = -2.5V	-0.32A
	3.4Ω @ V <sub>GS</sub> = -1.8V	-0.27A
	5.0Ω @ V <sub>GS</sub> = -1.5V	-0.22A

#### **Features and Benefits**

- Low On-Resistance
- Low Input/Output Leakage
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

## **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Power-management functions
- Backlighting
- Load switches

#### **Mechanical Data**

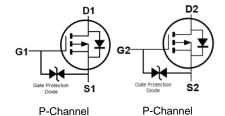
- Package: X2-DFN1010-6
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208
- Weight: 0.0015 grams (Approximate)

#### X2-DFN1010-6 (Type UXC)

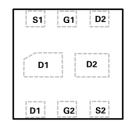




Bottom View



Equivalent Circuit



Pinout Top View

## **Ordering Information** (Note 4)

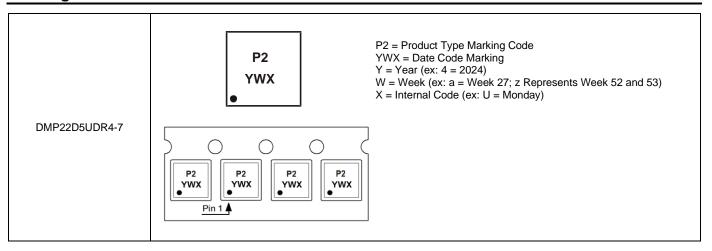
Orderable Part Number	Paakaga	Tape Width (mm)	Vidth (mm) Tape Pitch (mm)		Packing		
	Package	rape widin (min)	Tape Fitch (IIIII)	Qty.	Carrier		
DMP22D5UDR4-7	X2-DFN1010-6 (Type UXC)	8	4	5,000	Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# **Marking Information**



#### Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	2	3	4	5	6	7	8	9	0	1	2	3
Week	Week 1-26			27-52			53					
Code	A-Z			A-Z a-z z			Z					
Internal Code	Sur	1	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	V	V	X		Υ		7

## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±8	V		
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	-4.5V Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		ID	-0.36 -0.29	А
Maximum Continuous Body Diode Forward Curren	Is	-0.3A	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	Ірм	-0.8	Α		

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.38	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	328	°C/W
Total Power Dissipation (Note 6)		PD	0.66	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	190	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.



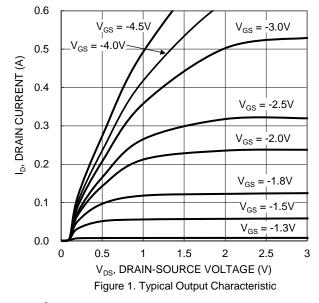
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	-20	-	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current @Tc = +25°C	IDSS	1	1	-1	μΑ	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	l	-	±10	μA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(th)	-0.4	1	-1.0	٧	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
		l	1.6	1.9		$V_{GS} = -4.5V, I_{D} = -100mA$	
Static Drain-Source On-Resistance	D- avan	l	2.2	2.4	Ω	$V_{GS} = -2.5V, I_D = -50mA$	
Static Dialii-Source Off-Resistance	R <sub>DS(ON)</sub>	l	3.2	3.4		Vgs = -1.8V, ID = -20mA	
		l	4.1	5.0		$V_{GS} = -1.5V, I_{D} = -10mA$	
Diode Forward Voltage	$V_{SD}$		-0.75	-1.1	V	$V_{GS} = 0V$ , $I_S = -10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		17	_			
Output Capacitance	Coss	_	4.1	_	pF	$V_{DS} = -16V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		2.7	_		1 – 1.01/11/12	
Total Gate Charge	Qg		0.3	_		15)/ )/ 40)/	
Gate-Source Charge	Qgs		0.04	_	nC	V <sub>G</sub> S = -4.5V, V <sub>D</sub> S = -10V I <sub>D</sub> = -250mA	
Gate-Drain Charge	$Q_{gd}$		0.1	_		ID = -230IIIA	
Turn-On Delay Time	t <sub>D(ON)</sub>		7.3	_			
Turn-On Rise Time	t <sub>R</sub>	_	20.7	_	nc	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -4.5V	
Turn-Off Delay Time	tD(OFF)	_	185	_	ns	$R_G = 2\Omega$ , $I_D = -200mA$	
Turn-Off Fall Time	t <sub>F</sub>	_	97	_			

Notes:

<sup>7.</sup> Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.





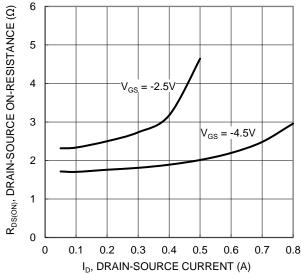


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

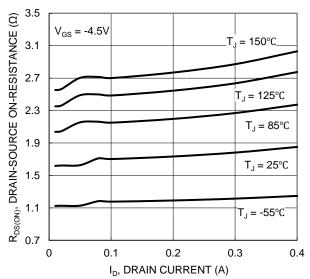
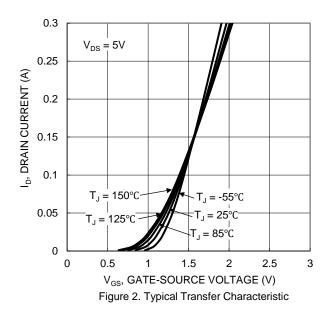
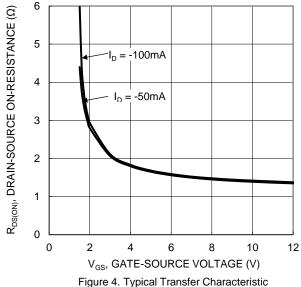


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





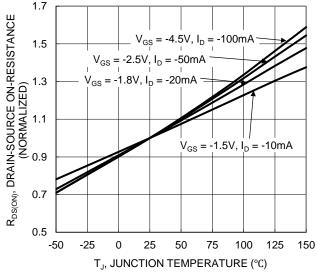


Figure 6. On-Resistance Variation with Junction Temperature



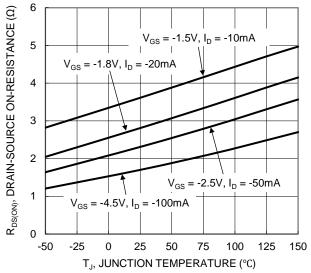
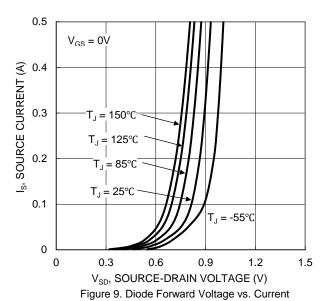


Figure 7. On-Resistance Variation with Junction Temperature



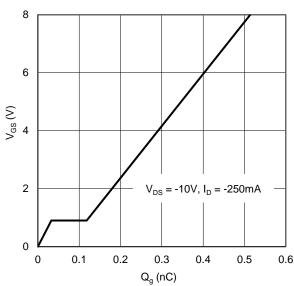


Figure 11. Gate Charge

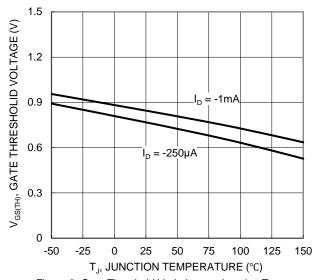
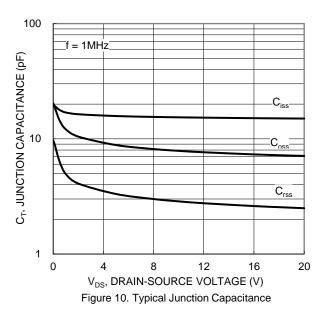


Figure 8. Gate Threshold Variation vs. Junction Temperature



1 R<sub>DS(ON)</sub> ID, DRAIN CURRENT (A) Pw = 10ms $T_{J(Max)} = 150$ °C  $T_A = 25$ °C Pw = 100ms Single Pulse Pw = 1sDUT on 1\*MRP = 10s**Board** DC V<sub>GS</sub>= -4.5V 0.01 0.1 10 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



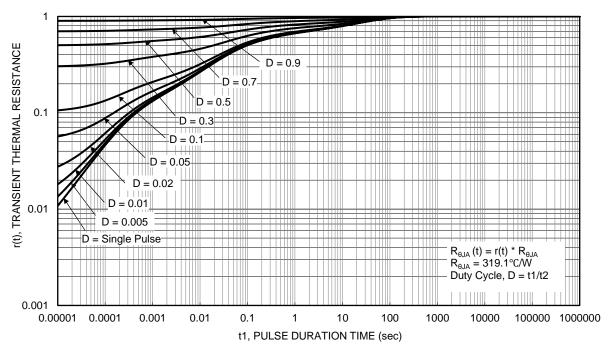


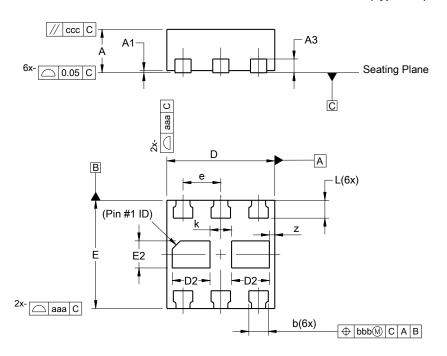
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-DFN1010-6 (Type UXC)

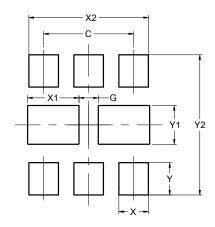


X2-DFN1010-6								
(Type UXC)								
Dim	Min	Max	Тур					
Α		0.40	0.39					
A1		0.05						
A3			0.127					
b	0.13	0.23	0.18					
D	0.95	1.05	1.00					
D2	0.30	0.40	0.35					
Е	0.95	1.05	1.00					
E2	0.20	0.30	0.25					
е	0.	350 BS	С					
١	0.115	0.215	0.165					
k			0.20					
Z	0.02 0.08 0.09							
aaa	0.08							
bbb	0.07							
CCC	0.05							
All Dimensions in mm								

# **Suggested Pad Layout**

 $\label{prop:package-outlines.html} Please see \ http://www.diodes.com/package-outlines.html \ for the \ latest \ version.$ 

## X2-DFN1010-6 (Type UXC)



Dimensions	Value
Dillielisiolis	(in mm)
C	0.700
G	0.300
Х	0.230
X1	0.450
X2	0.930
Υ	0.250
Y1	0.300
Y2	1.085



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